

Fig. 1 PRIOR ART

PACKAGE TYPE	TSOP	CSP	PRODUCT SPECIFICATIONS Max/Min
TERMINAL CAPACITANCE IN PACKAGE	1. 00	0. 14	3. 50/2. 50

Fig. 2A PRIOR ART

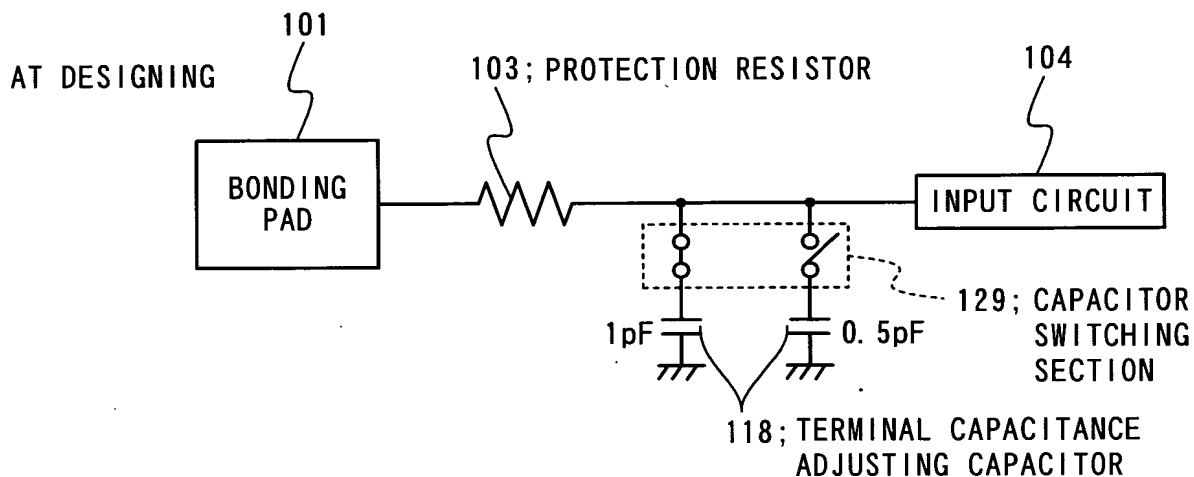


Fig. 2B PRIOR ART

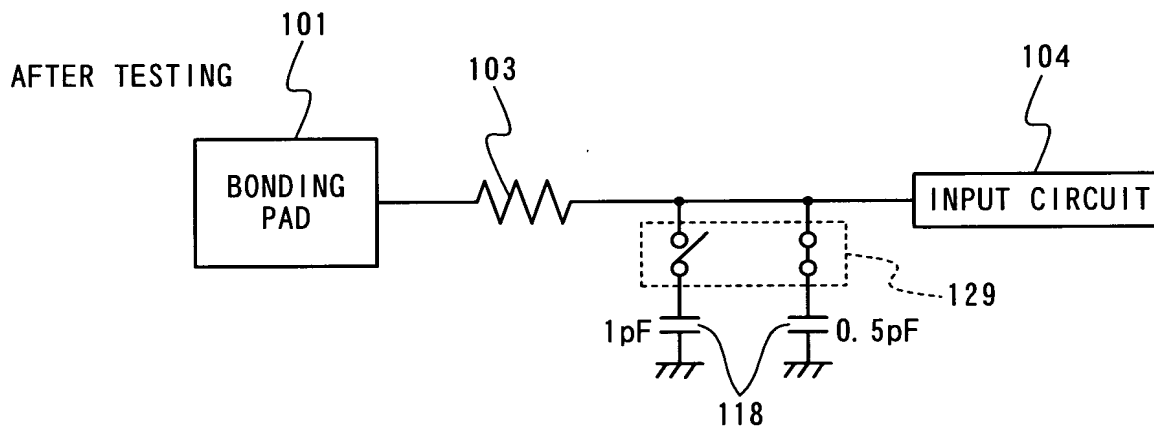


Fig. 3 PRIOR ART

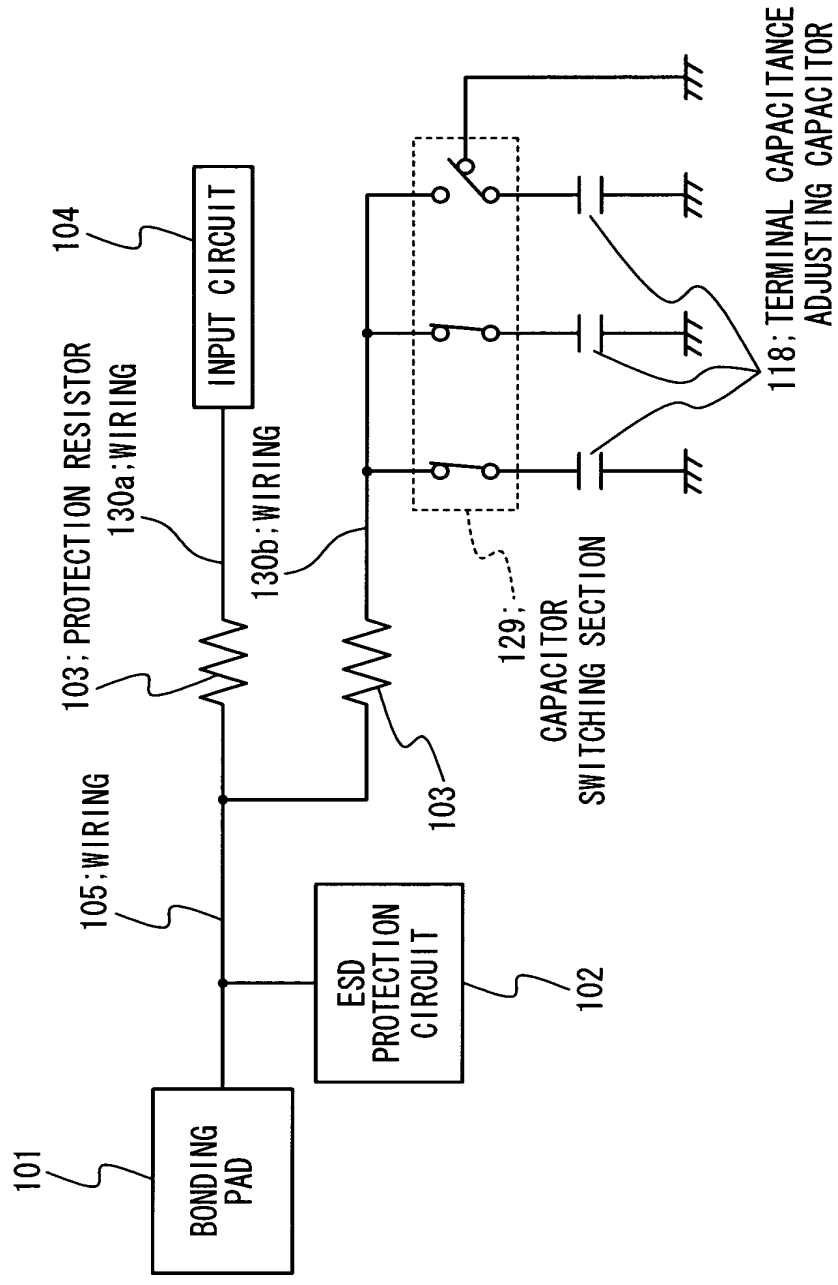


Fig. 4 PRIOR ART

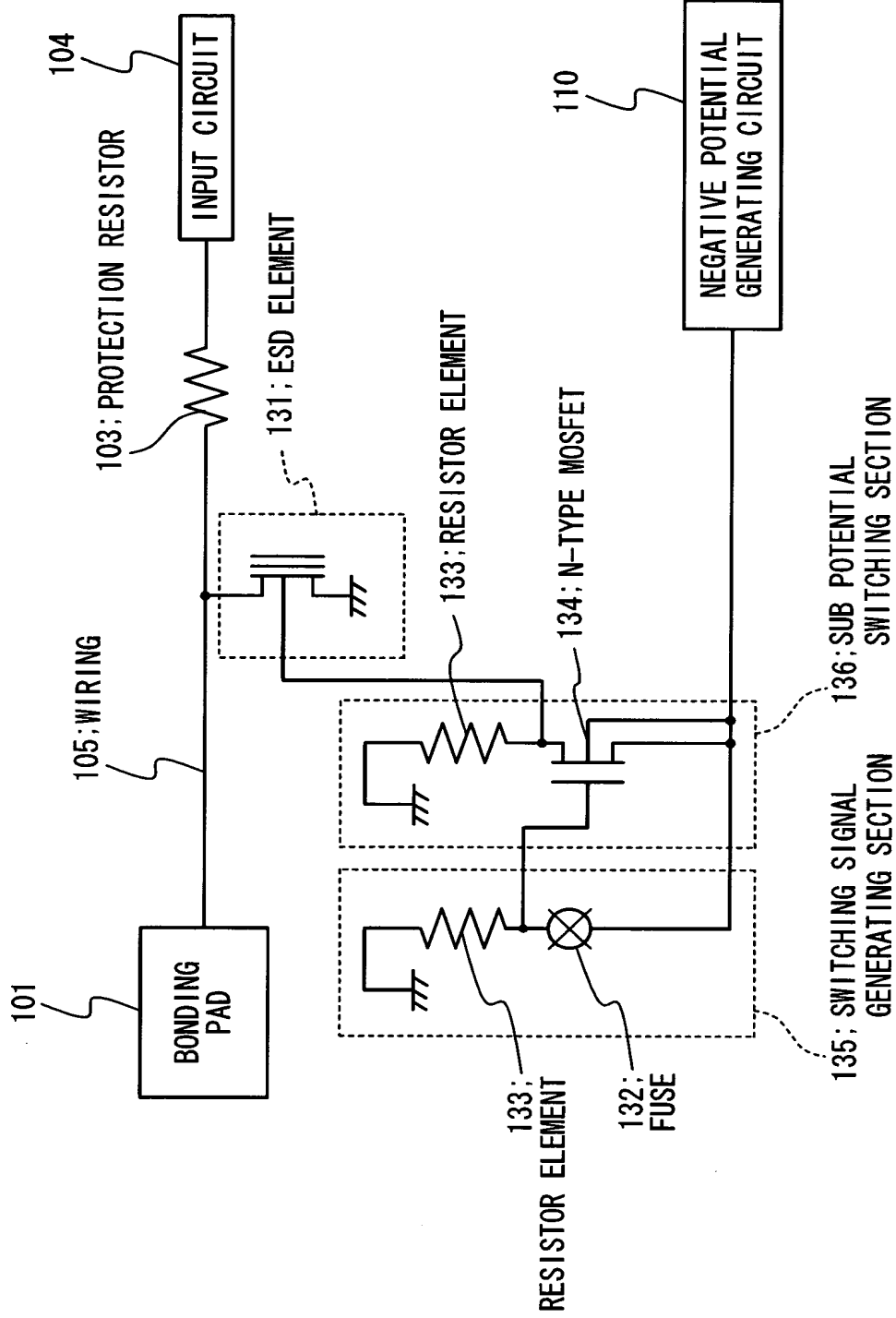


Fig. 5A

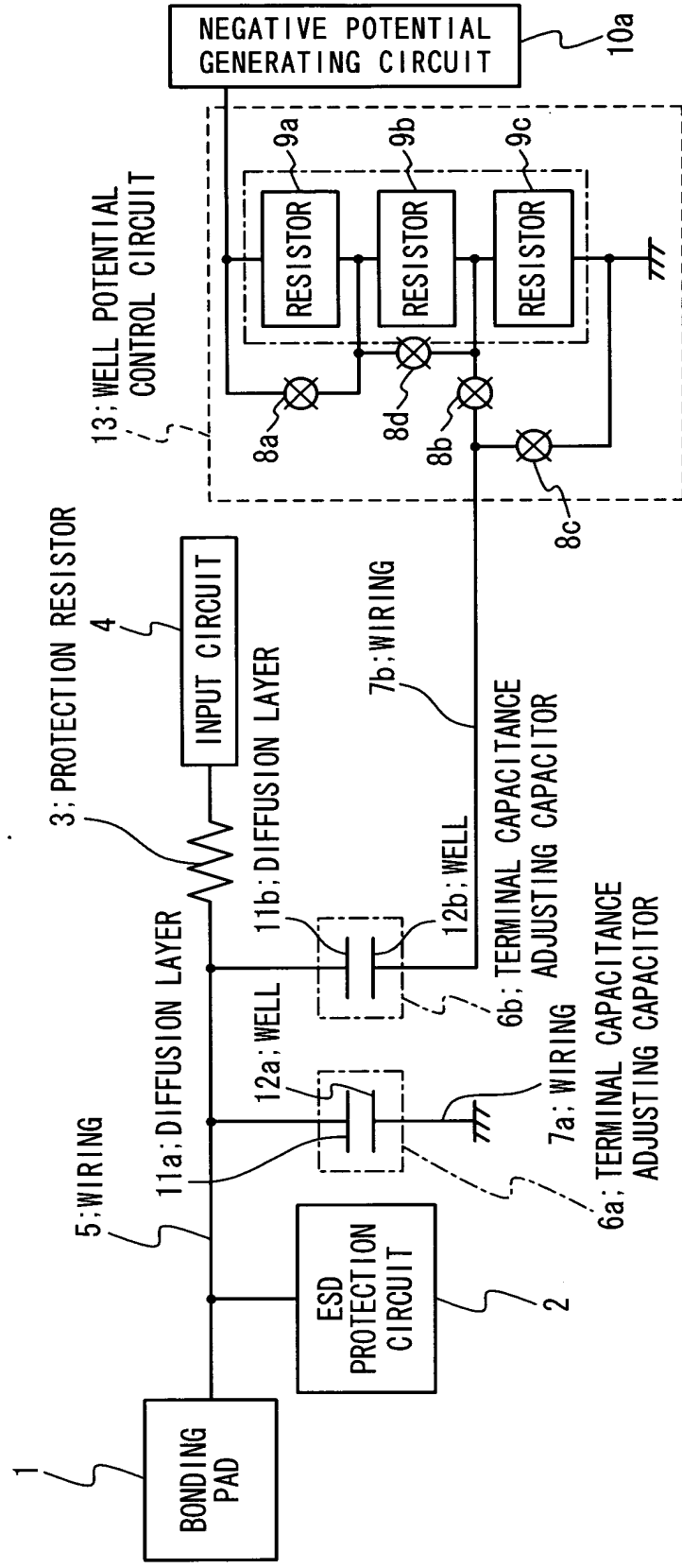
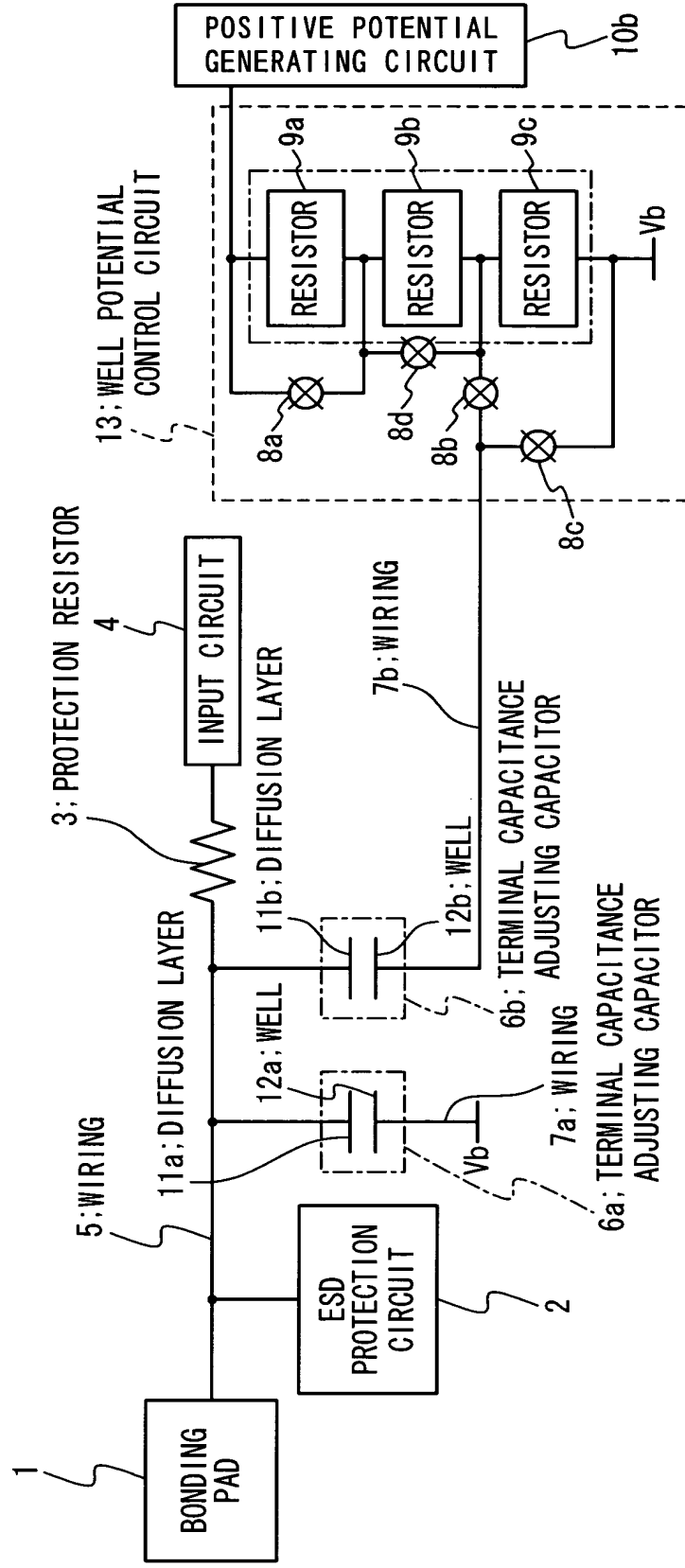


Fig. 5B



F i g . 6

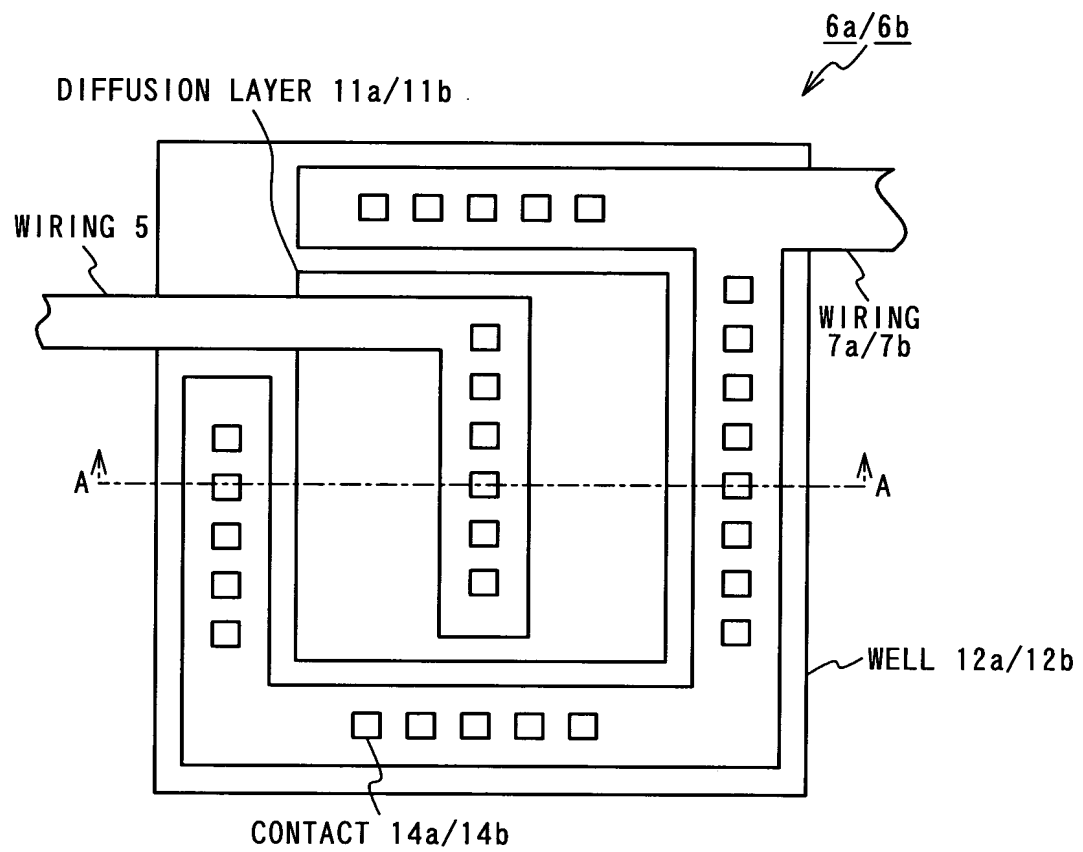


Fig. 7

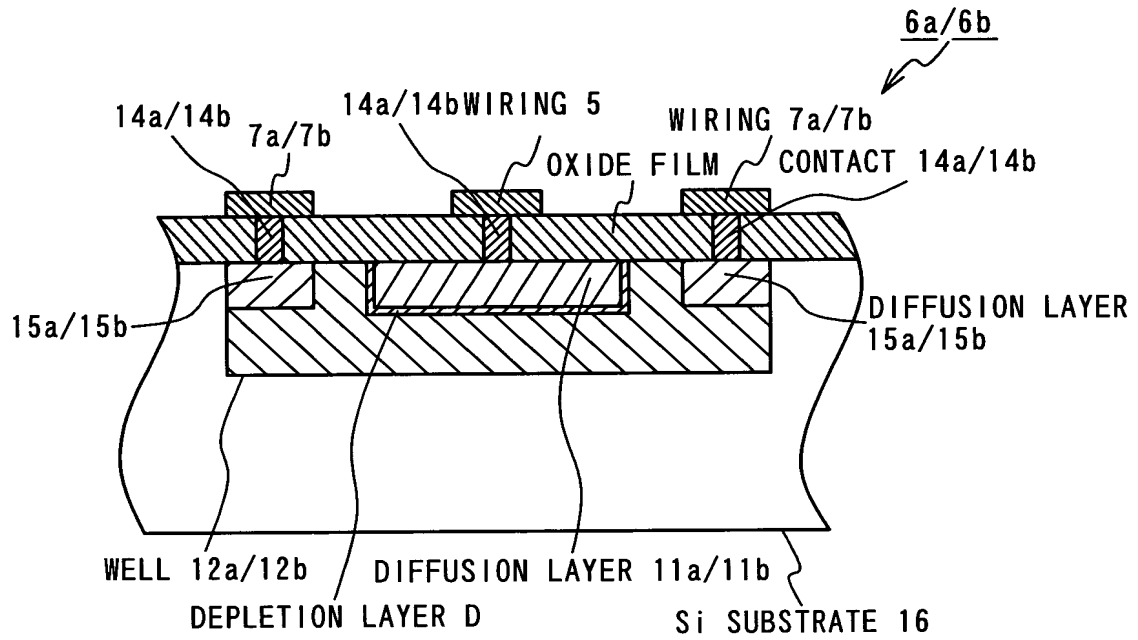


Fig. 8

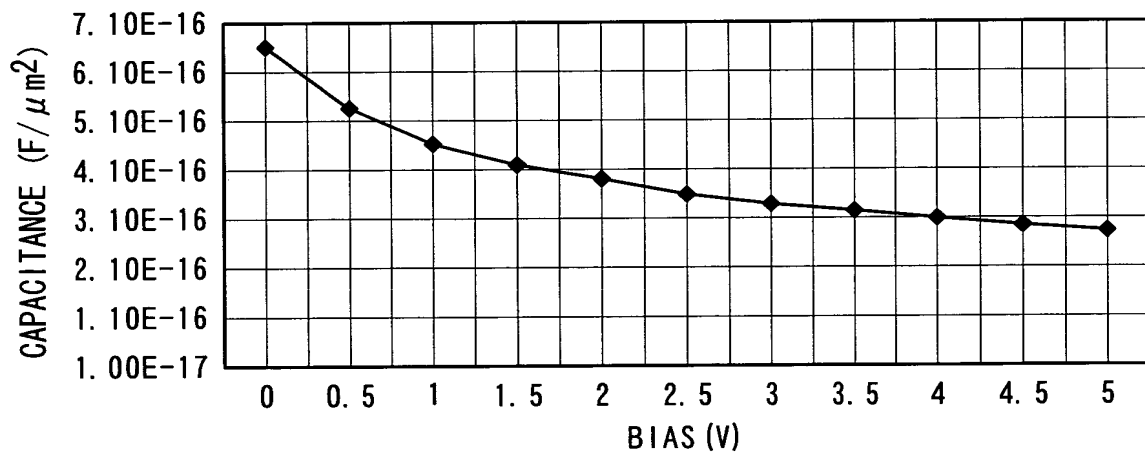


Fig. 9

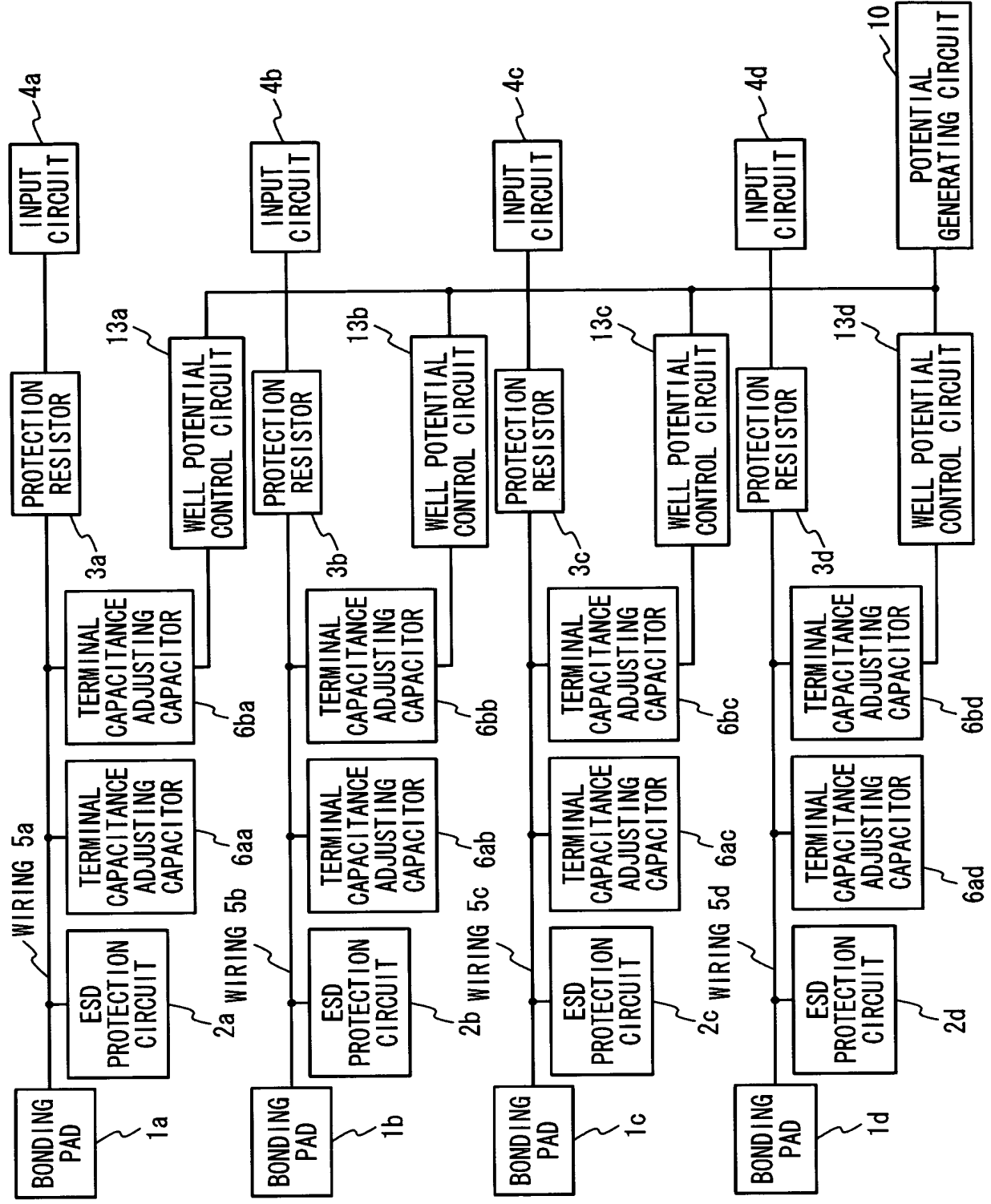


Fig. 10

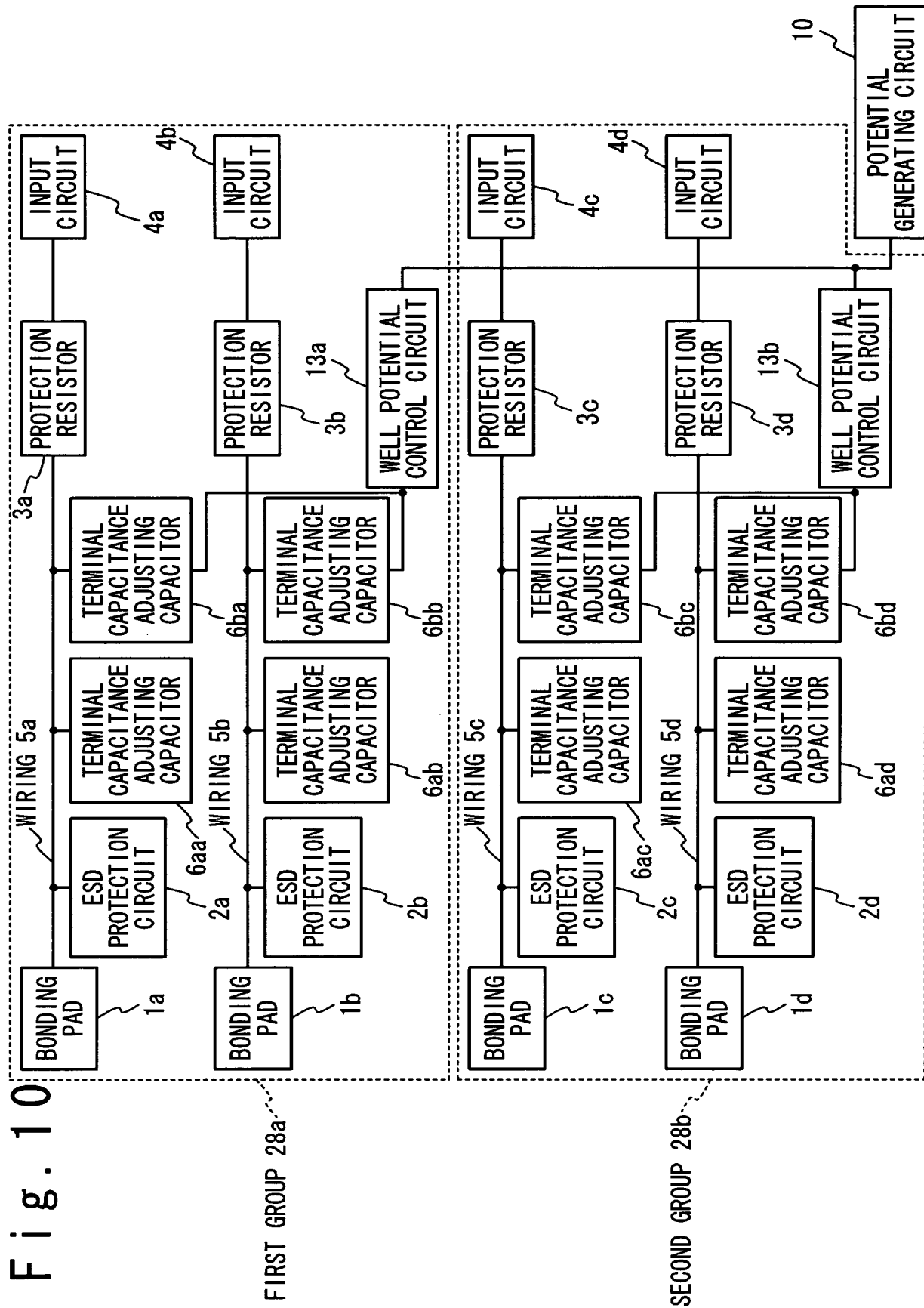
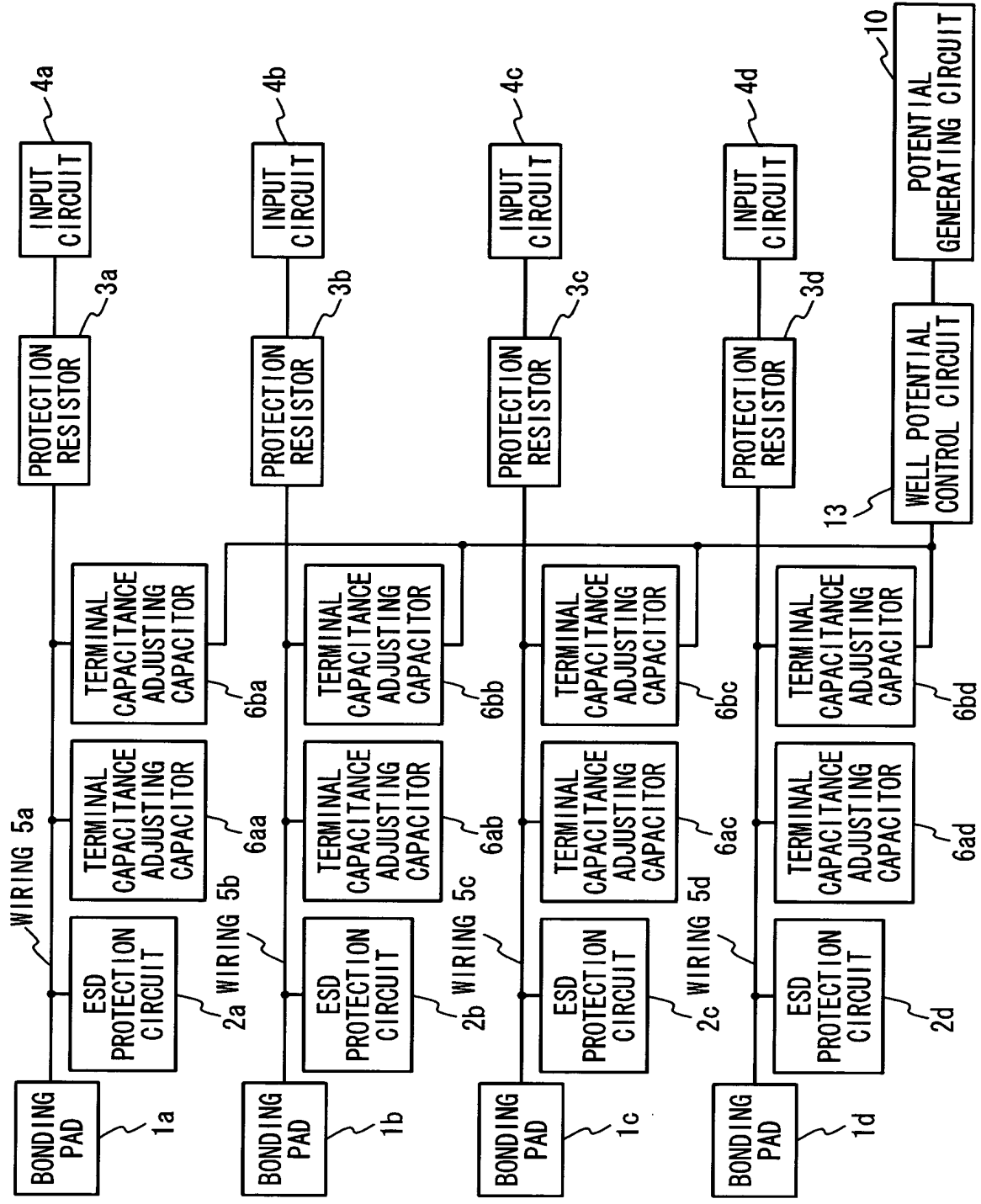
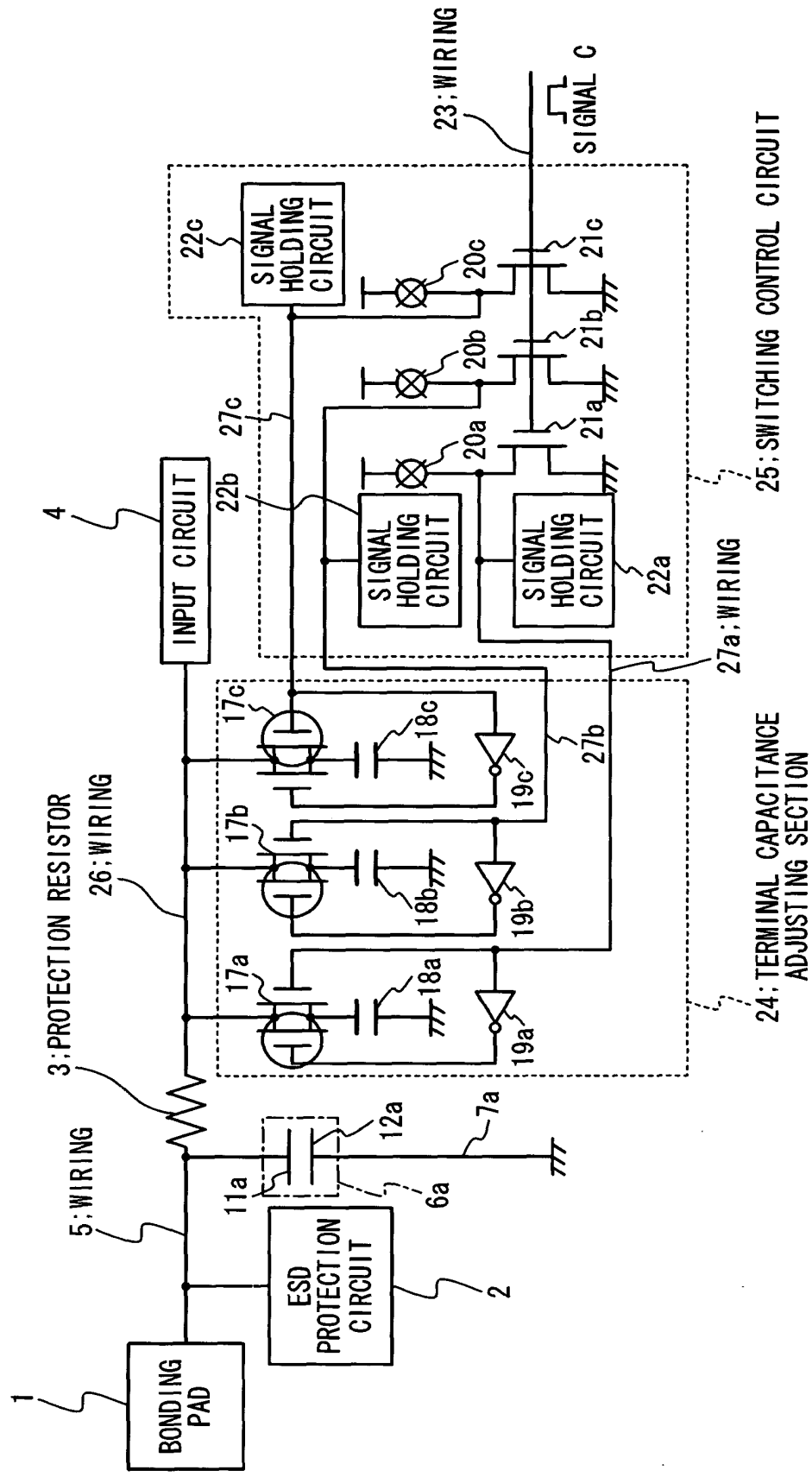


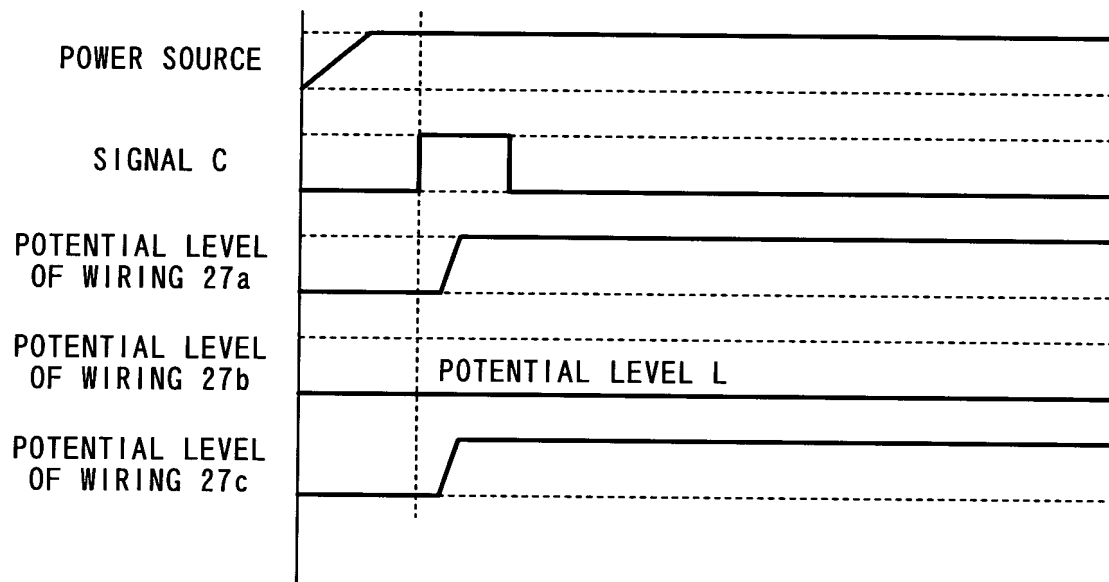
Fig. 11



1: BONDING PAD
 2: ESD PROTECTION CIRCUIT
 3: PROTECTION RESISTOR
 4: INPUT CIRCUIT
 5: WIRING
 6: WIRING
 7: WIRING
 11a: CAPACITOR
 12a: CAPACITOR
 17a, 17b, 17c: DIODES
 18a, 18b, 18c: DIODES
 19a, 19b, 19c: DIODES
 20a, 20b, 20c: TRANSISTORS
 21a, 21b, 21c: TRANSISTORS
 22a, 22b, 22c: SIGNAL HOLDING CIRCUIT
 23: WIRING
 24: TERMINAL CAPACITANCE ADJUSTING SECTION
 25: SWITCHING CONTROL CIRCUIT
 26: WIRING
 27a: WIRING
 27b: WIRING
 27c: WIRING
 SIGNAL C



F i g . 1 3



F i g . 1 4

	1	2	3	4	5	6	7	8
FUSE 20a	○	×	×	○	○	○	×	×
FUSE 20b	○	○	×	○	×	×	○	×
FUSE 20c	○	○	○	×	×	○	×	×
TOTAL TERMINAL CAPACITANCE	3pF	2pF	0pF	6pF	4pF	1pF	5pF	3pF

Fig. 15

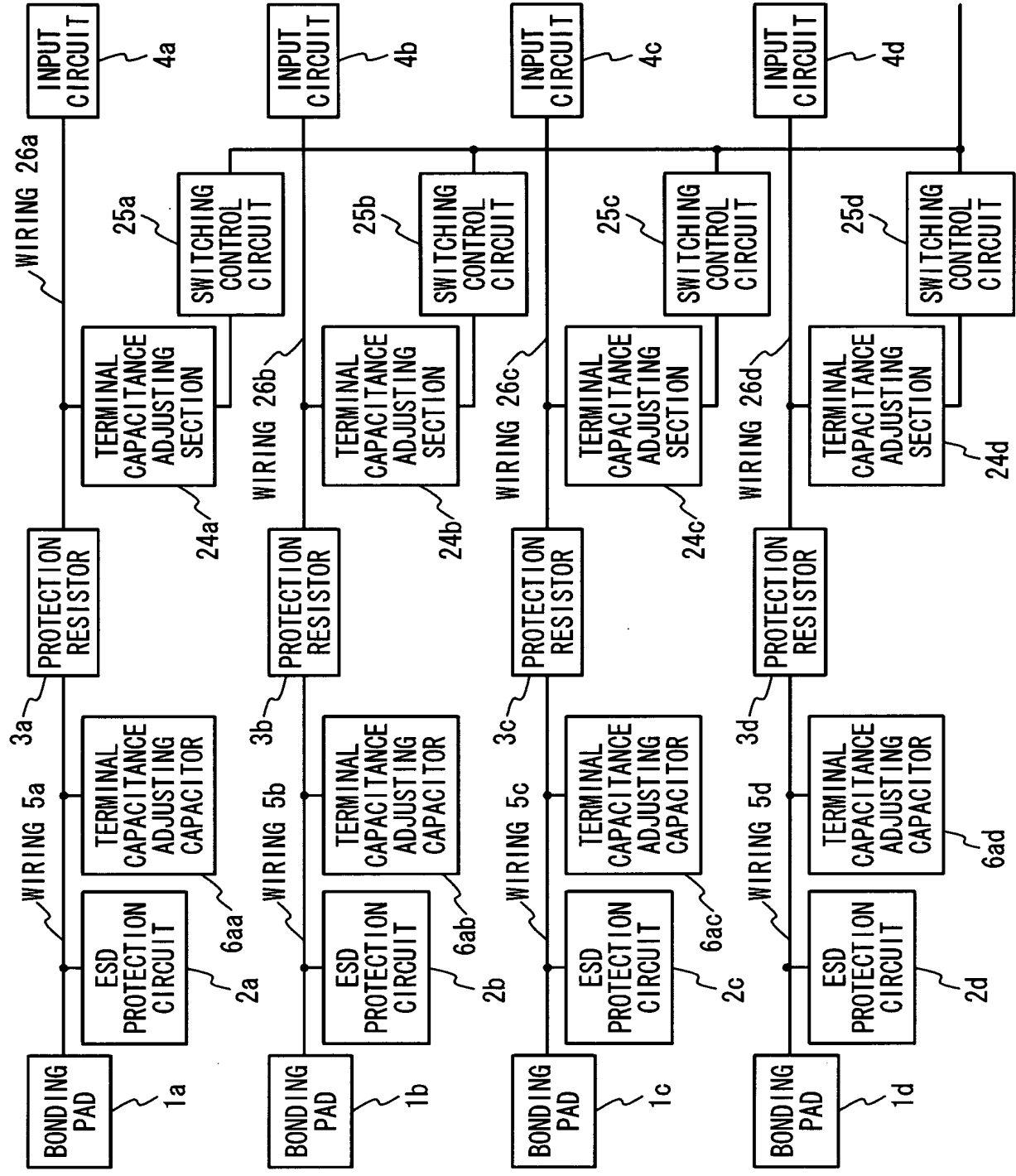


Fig. 16

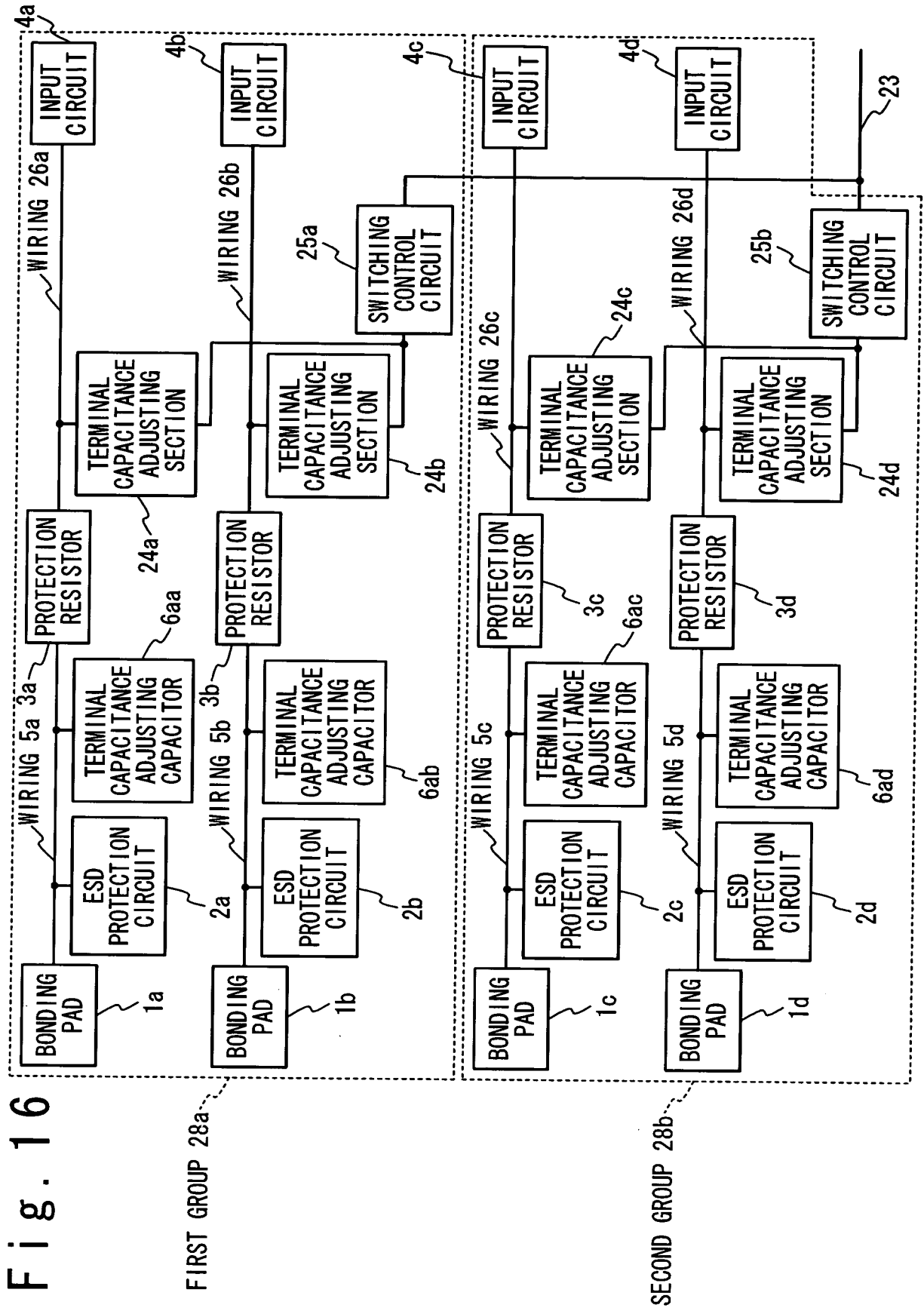
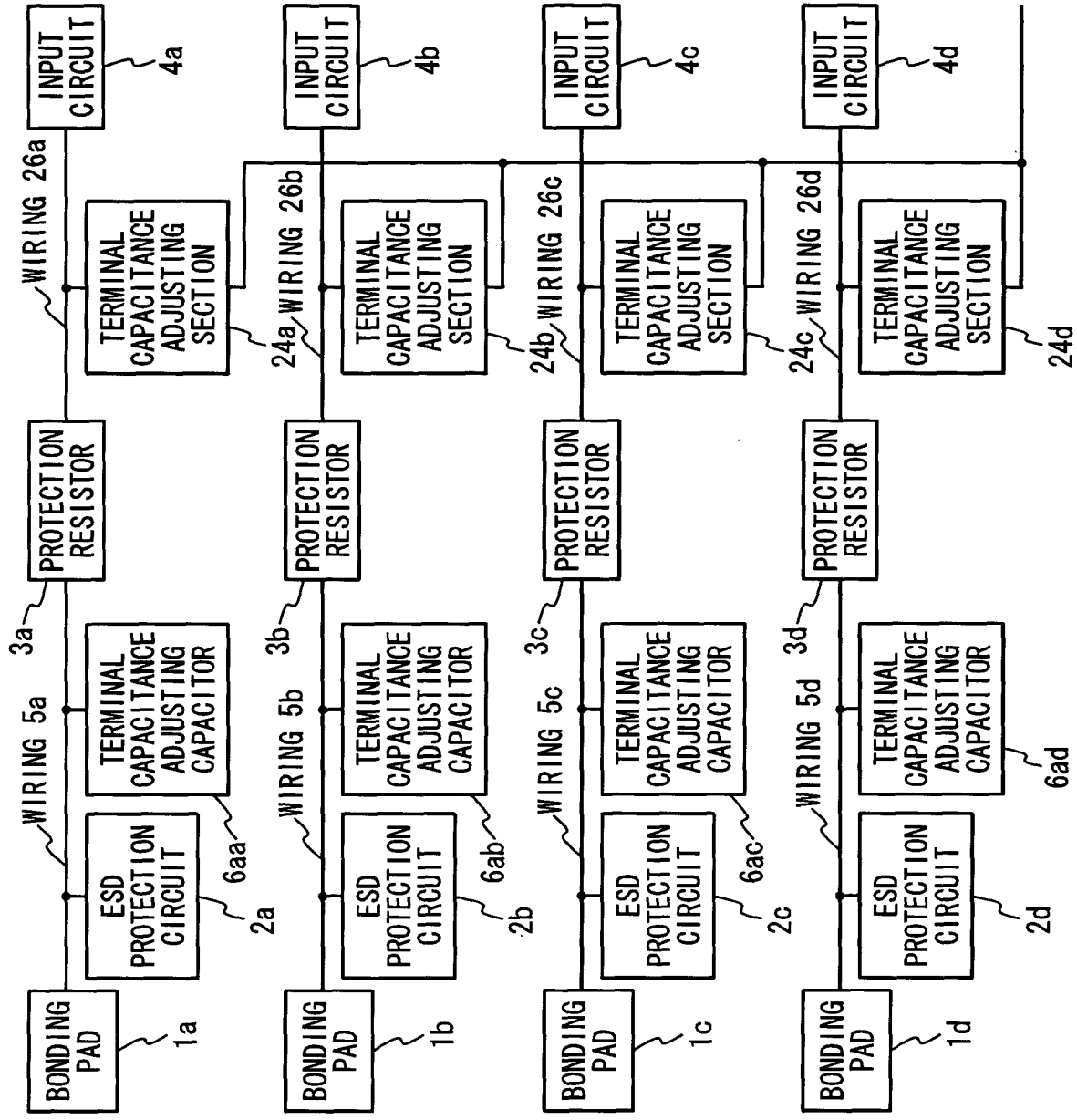


Fig. 17



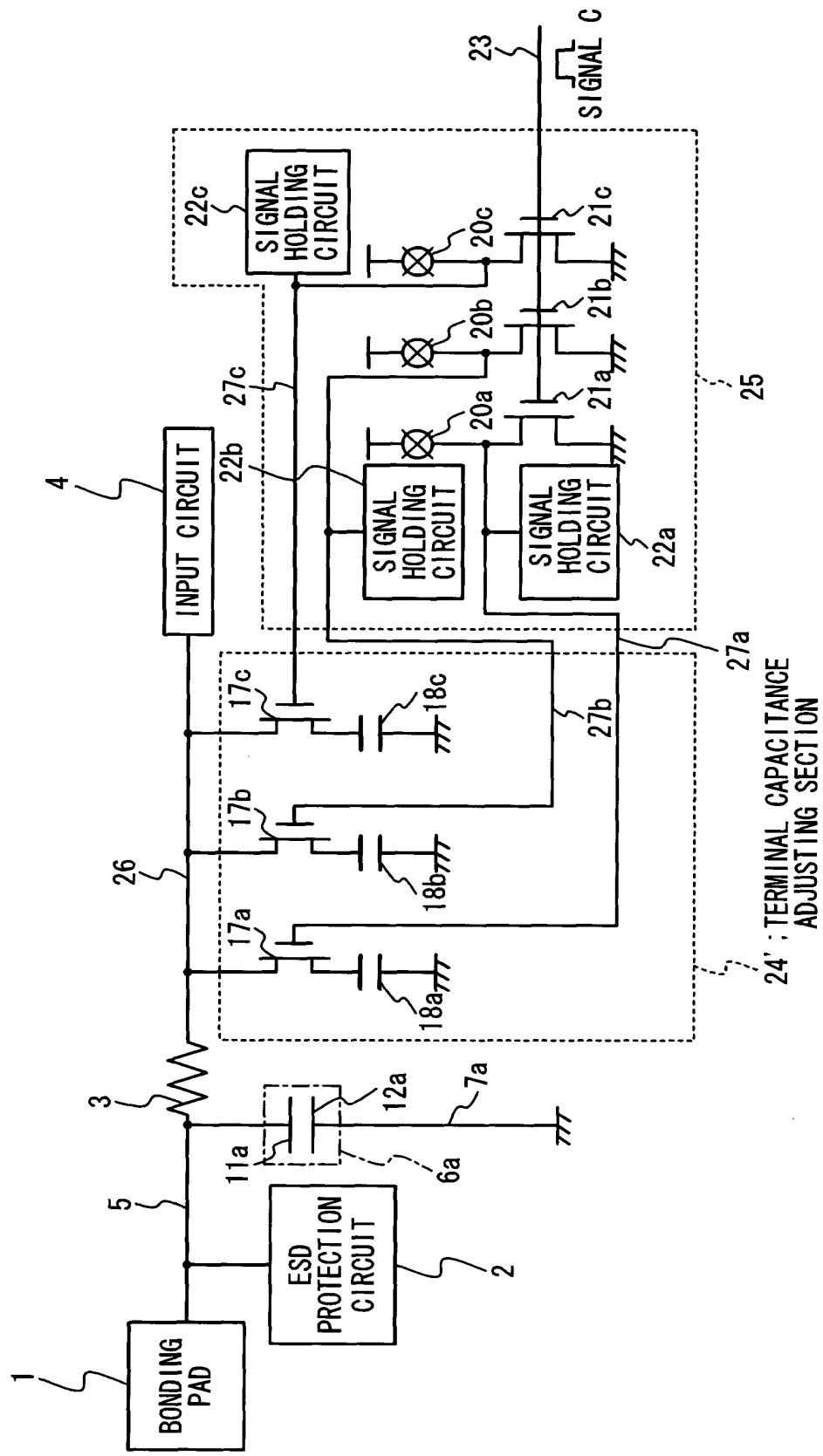
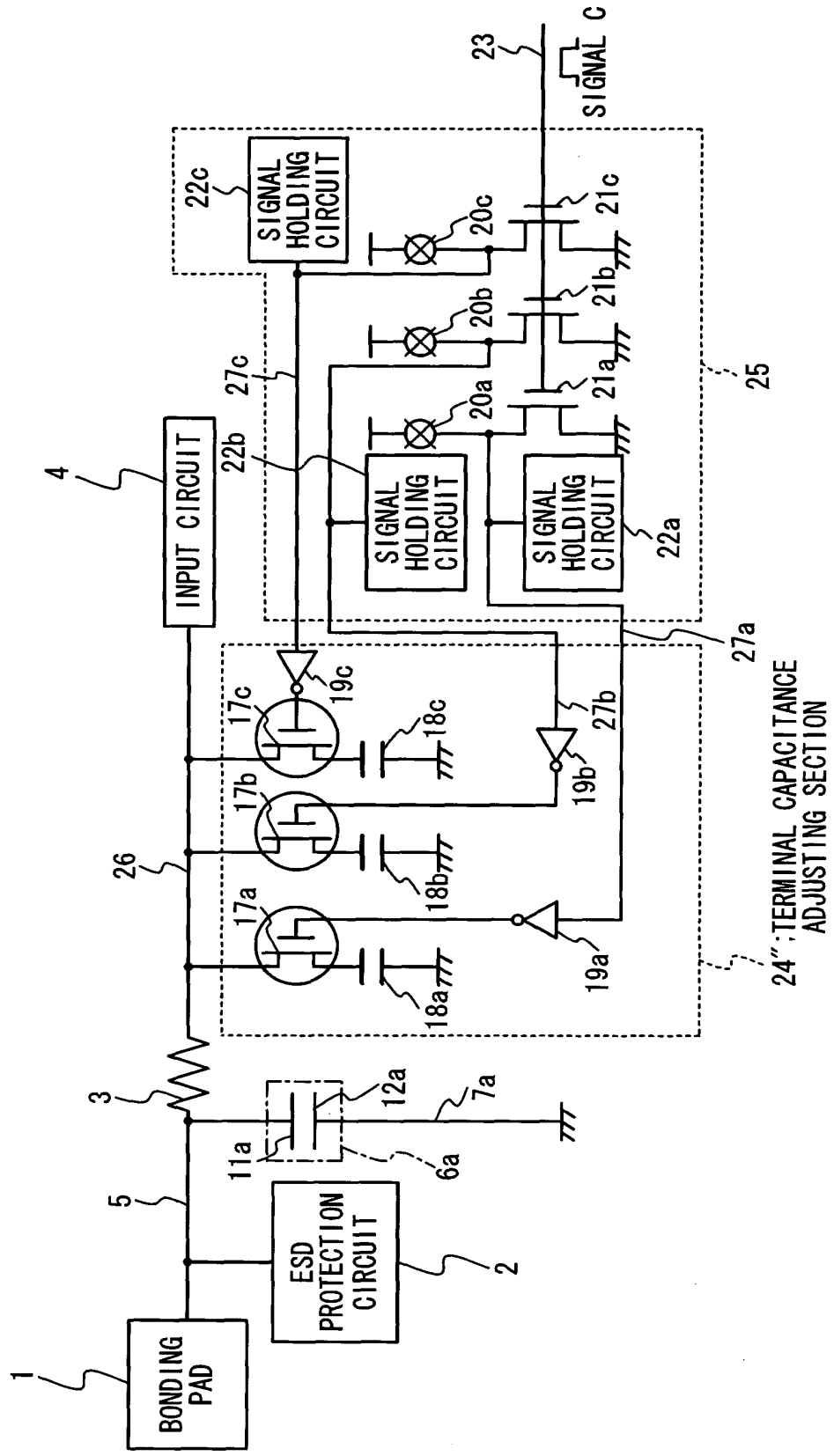


Fig. 19



The schematic diagram illustrates the internal circuitry of a semiconductor device 1. It features a bonding pad 1 connected to an ESD protection circuit 2, which includes a diode 11a and a capacitor 12a. A resistor 3 is connected to the ESD protection circuit 2 and an input circuit 4. The input circuit 4 contains a resistor 5 and is connected to a switching control circuit 25. The switching control circuit 25 is composed of three signal holding circuits 22a, 22b, and 22c, each with a transistor 20a, 20b, or 20c and a signal holding circuit 21a, 21b, or 21c. The switching control circuit 25 is connected to a signal line 23 and a signal C input.

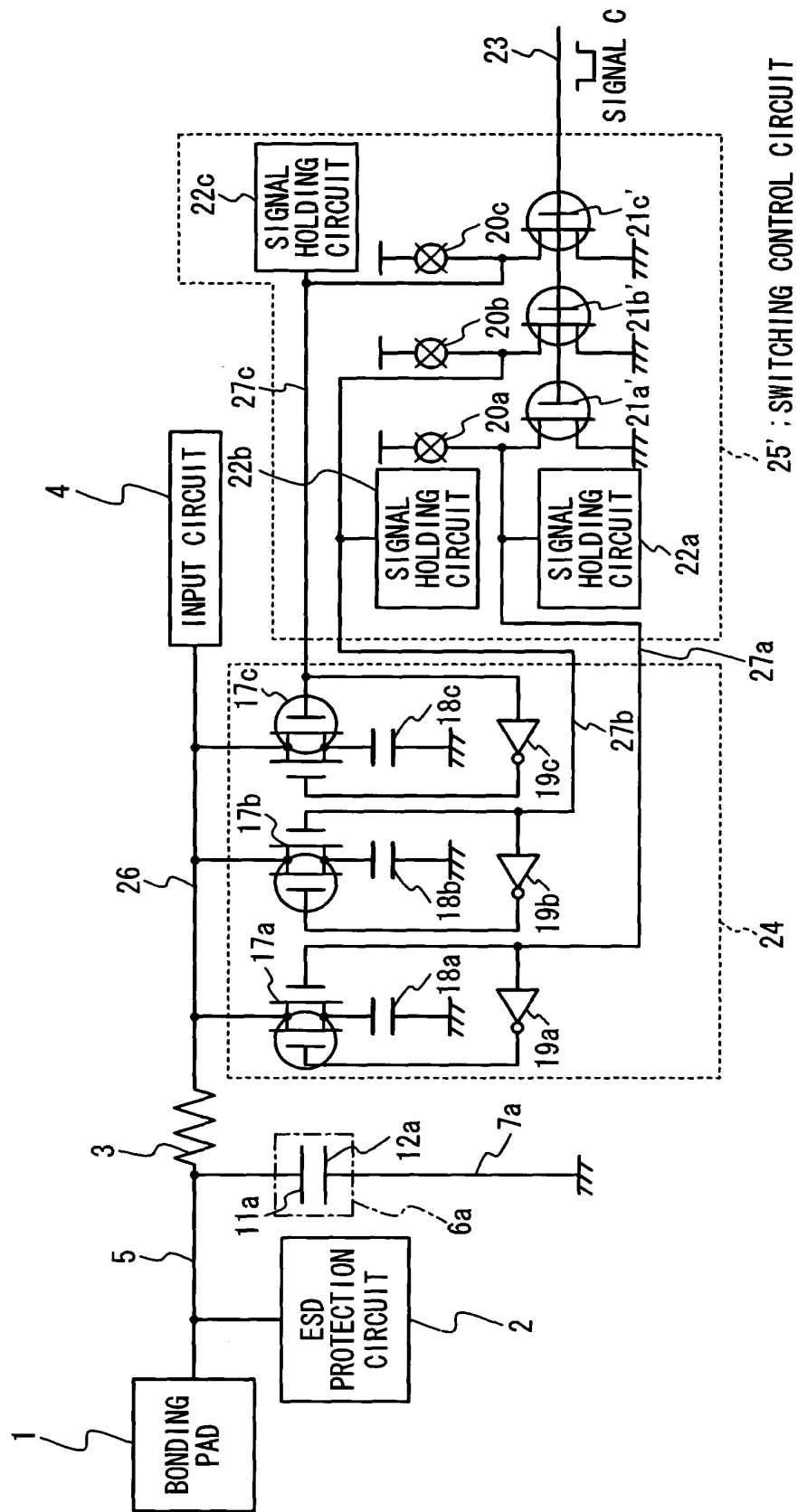


Fig. 21

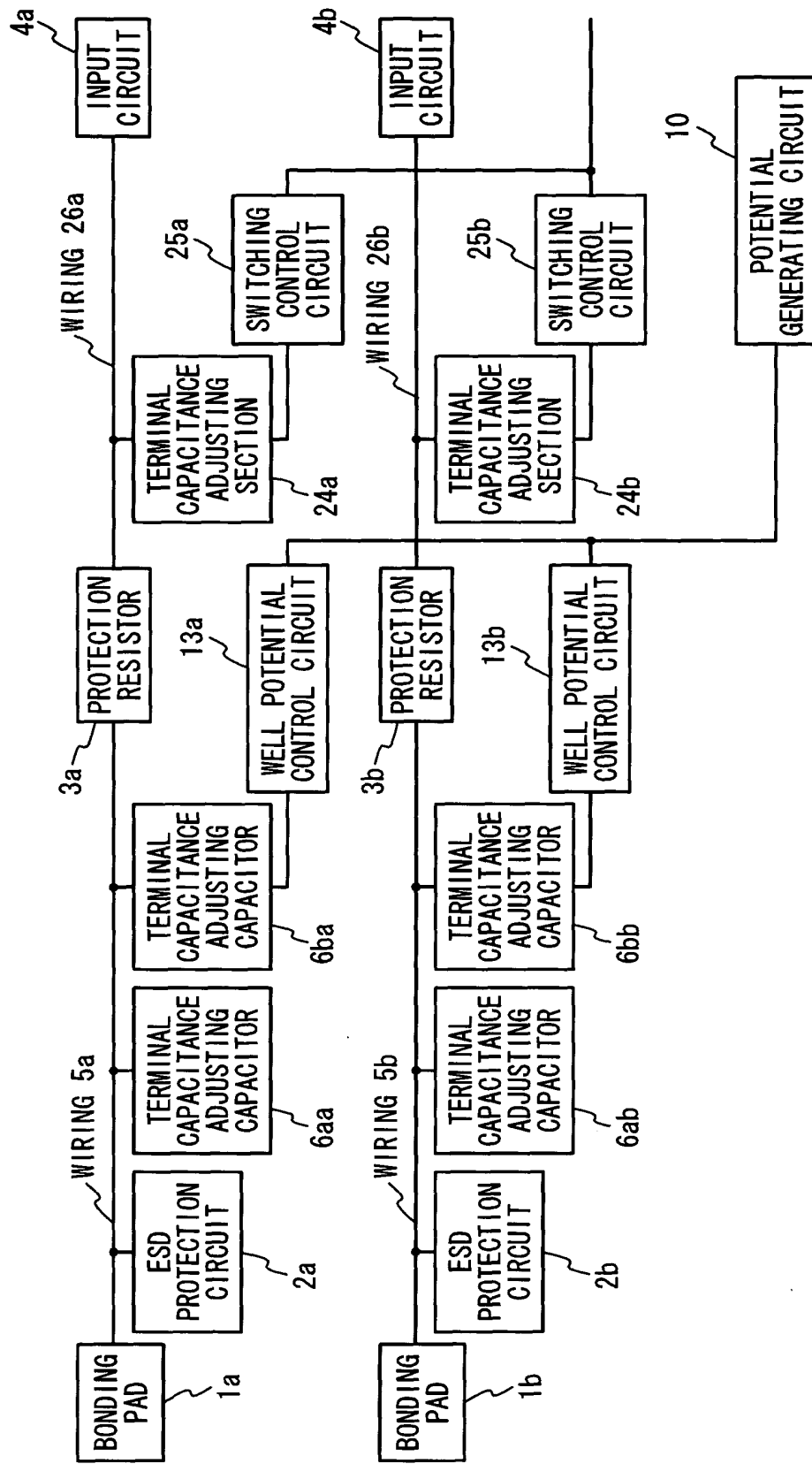


Fig. 22

